

74LCX821

Low-Voltage 10-Bit D-Type Flip-Flop with 5V Tolerant Inputs and Outputs

General Description

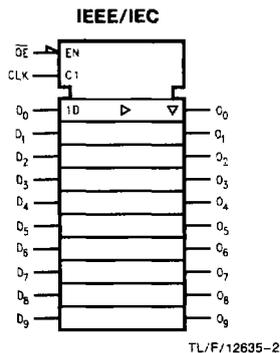
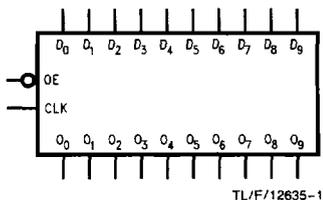
The LCX821 consists of ten D-type Flip-Flops with TRI-STATE® outputs for bus organized system applications. The device is designed for low voltage (3.3V) V_{CC} applications with capability of interfacing to a 5V signal environment.

The LCX821 is fabricated with an advanced CMOS technology to achieve high speed operation while maintaining CMOS low power dissipation.

Features

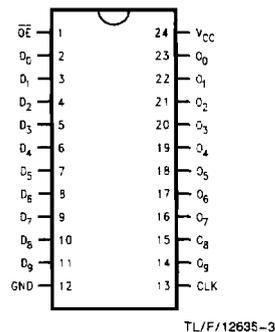
- 5V tolerant inputs and outputs
- 8.5 ns t_{PD} max, 10 μA I_{CCQ} max
- Power-down high impedance inputs and outputs
- Support live insertion/withdrawal
- 2.0V–3.6V V_{CC} supply operation
- ± 24 mA output drive
- Implements patented Quiet Series™ noise/EMI reduction circuitry
- Functionally compatible with the 74 series 821
- Latch-up performance exceeds 500 mA
- ESD performance:
 - Human Body Model > 2000V
 - Machine Model > 200V

Logic Symbols



Connection Diagram

Pin Assignment for SOIC, SSOP and TSSOP



Pin Names	Description
D ₀ –D ₉	Data Inputs
CLK	Clock Input
\overline{OE}	Output Enable Input
O ₀ –O ₉	TRI-STATE Latch Outputs

	SOIC JEDEC	SSOP Type II	TSSOP JEDEC
Order Number	74LCX821WM 74LCX821WMX	74LCX821MSA 74LCX821MSAX	74LCX821MTC 74LCX821MTCX
See NS Package Number	M24B	MSA24	MTC24

Functional Description

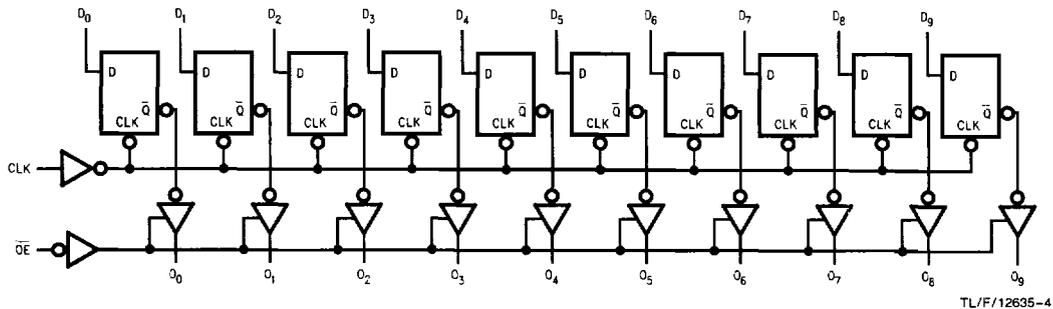
The LCX821 consists of ten edge-triggered flip-flops with individual D-type inputs with TRI-STATE true outputs. The buffered clock and buffered Output Enable are common to all flip-flops. The ten flip-flops will store the state of their individual D inputs that meet the setup and hold time requirements on the LOW-to-HIGH Clock (CLK) transition. With the Output Enable (\overline{OE}) LOW, the contents of the ten flip-flops are available at the outputs. When \overline{OE} is HIGH, the outputs go to the high impedance state. Operation of the \overline{OE} input does not affect the state of the flip-flops.

Function Table

Inputs			Internal	Outputs	Function
\overline{OE}	CLK	D	Q	O_n	
H	H	L	NC	Z	Hold
H	H	H	NC	Z	Hold
H	↗	L	L	Z	Load
H	↗	H	H	Z	Load
L	↗	L	L	L	Data Available
L	↗	H	H	H	Data Available
L	H	L	NC	NC	No Change in Data
L	H	H	NC	NC	No Change in Data

H = HIGH Voltage Level
 L = LOW Voltage Level
 X = Immaterial
 Z = High Impedance
 ↗ = LOW-to-HIGH Transition
 NC = No Change

Logic Diagram



Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Symbol	Parameter	Value	Conditions	Units
V_{CC}	Supply Voltage	-0.5 to +7.0		V
V_I	DC Input Voltage	-0.5 to +7.0		V
V_O	DC Output Voltage	-0.5 to +7.0	Output in TRI-STATE	V
		-0.5 to $V_{CC} + 0.5$	Output in High or Low State (Note 2)	V
I_{IK}	DC Input Diode Current	-50	$V_I < GND$	mA
I_{OK}	DC Output Diode Current	-50	$V_O < GND$	mA
		+50	$V_O > V_{CC}$	
I_O	DC Output Source/Sink Current	± 50		mA
I_{CC}	DC Supply Current per Supply Pin	± 100		mA
I_{GND}	DC Ground Current per Ground Pin	± 100		mA
T_{STG}	Storage Temperature	-65 to +150		$^{\circ}C$

Note 1: The Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. The device should not be operated at these limits. The parametric values defined in the "Electrical Characteristics" table are not guaranteed at the Absolute Maximum Ratings. The "Recommended Operating Conditions" table will define the conditions for actual device operation.

Note 2: I_O Absolute Maximum Rating must be observed.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units	
V_{CC}	Supply Voltage	Operating	2.0	3.6	V
		Data Retention	1.5	3.6	
V_I	Input Voltage	0	5.5	V	
V_O	Output Voltage	HIGH or LOW State	0	V_{CC}	V
		TRI-STATE	0	5.5	
I_{OH}/I_{OL}	Output Current	$V_{CC} = 3.0V-3.6V$ $V_{CC} = 2.7V$	± 24 ± 12	mA	
T_A	Free-Air Operating Temperature	-40	85	$^{\circ}C$	
$\Delta t/\Delta V$	Input Edge Rate, $V_{IN} = 0.8V-2.0V$, $V_{CC} = 3.0V$	0	10	ns/V	

DC Electrical Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	$T_A = -40^{\circ}C$ to $+85^{\circ}C$		Units
				Min	Max	
V_{IH}	HIGH Level Input Voltage		2.7-3.6	2.0		V
V_{IL}	LOW Level Input Voltage		2.7-3.6		0.8	V
V_{OH}	HIGH Level Output Voltage	$I_{OH} = -100 \mu A$	2.7-3.6	$V_{CC} - 0.2$		V
		$I_{OH} = -12 mA$	2.7	2.2		V
		$I_{OH} = -18 mA$	3.0	2.4		V
		$I_{OH} = -24 mA$	3.0	2.2		V
V_{OL}	LOW Level Output Voltage	$I_{OL} = 100 \mu A$	2.7-3.6		0.2	V
		$I_{OL} = 12 mA$	2.7		0.4	V
		$I_{OL} = 16 mA$	3.0		0.4	V
		$I_{OL} = 24 mA$	3.0		0.55	V
I_I	Input Leakage Current	$0 \leq V_I \leq 5.5V$	2.7-3.6		± 5.0	μA
I_{OZ}	TRI-STATE Output Leakage	$0 \leq V_O \leq 5.5V$ $V_I = V_{IH}$ or V_{IL}	2.7-3.6		± 5.0	μA
I_{OFF}	Power-Off Leakage Current	V_I or $V_O = 5.5V$	0		10	μA
I_{CC}	Quiescent Supply Current	$V_I = V_{CC}$ or GND	2.7-3.6		10	μA
		$3.6V \leq V_I$, $V_O \leq 5.5V$	2.7-3.6		± 10	μA
ΔI_{CC}	Increase in I_{CC} per Input	$V_{IH} = V_{CC} - 0.6V$	2.7-3.6		500	μA

AC Electrical Characteristics

Symbol	Parameter	$T_A = -40^\circ\text{C to } +85^\circ\text{C}$				Units
		$V_{CC} = 3.3V \pm 0.3V$		$V_{CC} = 2.7V$		
		Min	Max (Note 1)	Min	Max Note 1	
f_{max}	Maximum Clock Frequency	150				MHz
t_{PHL}	Propagation Delay	1.5	7.0	1.5	7.5	ns
t_{PLH}	CLK to O_n	1.5	7.0	1.5	7.5	
t_{PZL}	Output Enable Time	1.5	7.5	1.5	8.0	ns
t_{PZH}		1.5	7.5	1.5	8.0	
t_{PLZ}	Output Disable Time	1.5	6.5	1.5	7.0	ns
t_{PHZ}		1.5	6.5	1.5	7.0	
t_{OSHL}	Output to Output Skew (Note 2)		1.0			ns
t_{OSLH}			1.0			
t_S	Setup Time, D_n to CLK	2.5		2.5		ns
t_H	Hold Time, D_n to CLK	1.5		1.5		ns
t_W	CLK Pulse Width	3.3		3.3		ns

Note 1: The Maximum AC limits are design target. Actual performance will be specified upon completion of characterization.

Note 2: Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH to LOW (t_{OSHL}) or LOW to HIGH (t_{OSLH}).

Dynamic Switching Characteristics

Symbol	Parameter	Conditions	V_{CC} (V)	$T_A = 25^\circ\text{C}$	Units
				Typical	
V_{OLP}	Quiet Output Dynamic Peak V_{OL}	$C_L = 50\text{ pF}, V_{IH} = 3.3V, V_{IL} = 0V$	3.3	0.8	V
V_{OLV}	Quiet Output Dynamic Valley V_{OL}	$C_L = 50\text{ pF}, V_{IH} = 3.3V, V_{IL} = 0V$	3.3	-0.8	V

Capacitance

Symbol	Parameter	Conditions	Typical	Units
C_{IN}	Input Capacitance	$V_{CC} = \text{Open}, V_I = 0V \text{ or } V_{CC}$	7	pF
C_O	Output Capacitance	$V_{CC} = 3.3V, V_I = 0V \text{ or } V_{CC}$	8	pF
C_{PD}	Power Dissipation Capacitance	$V_{CC} = 3.3V, V_I = 0V \text{ or } V_{CC}, f = 10\text{ MHz}$	20	pF